

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-11. (Cancelled)

12. (Currently amended) A method for manufacturing a test sensor,
comprising:

forming a multiple layer device, including depositing a first metallic layer onto a substrate material by physical vapor deposition; depositing an intermediate, sacrificial layer on said metallic layer; and depositing an electrically non-conductive layer adjacent said ~~metallic~~ intermediate, sacrificial layer by plasma enhanced chemical vapor deposition; and

applying an amount of ~~laser~~ energy to said multiple layer device to selectively remove a portion of said intermediate, sacrificial layer, ~~thereby causing and a~~ corresponding portion of either said metallic layer or said non-conductive layer to be removed.

13. (Cancelled)

14. (Currently amended) The method of claim ~~43~~ 12, wherein said amount of ~~laser~~ energy is in the range of approximately 40 mJ/cm² to 450 mJ/cm².

15. (Currently amended) The method of claim ~~43~~ 12, wherein said ~~laser~~ energy is provided by ~~includes~~ an ion-beam.

16. (Currently amended) The method of claim ~~43~~ 12, wherein said ~~laser~~ energy is provided by ~~includes~~ an electron beam.

17. (Currently amended) The method of claim 43 12, wherein the metallic layer includes at least one of copper, silver, gold, platinum, palladium, nickel, or aluminum.
18. (Currently amended) The method of claim 43 12, wherein the electrically non-conductive layer has a thickness less than or substantially equal to 1 μm .
19. (Currently amended) The method of claim 43 12, wherein the intermediate, sacrificial layer is made of polytetrafluorethylene.
20. (Currently amended) The method of claim 19, wherein the intermediate, sacrificial layer is deposited onto said metallic layer by plasma enhanced chemical vapor deposition.
21. (Currently amended) The method of claim 43 12, wherein the substrate is made of a polymer material.
22. (Previously presented) The method of claim 21, wherein the substrate is flexible.
23. (Currently amended) The method of claim 43 12, further comprising: depositing at least one of a second metallic layer, a second intermediate, sacrificial layer, or a second non-metallic conductive layer on said multiple layer device.
24. (Currently amended) The method of claim 43 12, further comprising: removing said corresponding portion of said non-conductive layer.
25. (Currently amended) The method of claim 43 12, further comprising: performing plasma activation before depositing said metallic layer, said non-conductive layer, or said intermediate layer.

26. (New) The method of claim 12, wherein said energy is provided by a laser.
27. (New) The method of claim 12, wherein the intermediate, sacrificial layer is made of a Teflon-like compound.
28. (New) The method of claim 12, wherein the electrically non-conductive layer is made of a ceramic layer comprising MgO.
29. (New) The method of claim 12, wherein the electrically non-conductive layer is not suitable for laser ablation.